

Author index

- Abermann, R. 42, 43, 63, 66, 72, 73
 Achenbach, J. D. 163
 Akasaka, Y. 214
 Akiyama, K. 615
 Aksay, I. A. 256, 257, 258
 Akyuz, C. D. 431
 Alcalá, J. 12, 13
 Alexander, H. 413, 415
 Allen, H. G. 350
 Allen, M. G. 378
 Andersen, H. C. 615
 Anderson, G. P. 253
 Anderson, J. C. 42
 Andreussi, F. 350
 Andrews, E. H. 247
 Arakawa, T. 438, 441
 Arakawa, Y. 438, 441
 Aravas, N. 386
 Argon, A. S. 341, 342, 679, 680
 Arzt, E. 410, 411, 503, 516, 518, 519, 524, 525, 526,
 528, 529, 531, 534, 536, 537, 673, 678, 708
 Asaro, R. J. 557, 577
 Ashby, M. F. 323, 508, 510, 511, 513, 533
 Ast, D. B. 455, 602
 Atkinson, C. 278
 Audoly, B. 339
 Augustyniak, W. M. 62, 105, 107
 Auld, B. A. 186
- Bagchi, A. 281, 503, 506, 508
 Bahnck, D. 415
 Bain, J. A. 175
 Bajaj, R. 51
 Baker, S. P. 521, 524, 528, 529, 534, 537
 Baliabar, S. 577
 Balk, T. J. 410, 411, 525, 526
 Ballarini, R. 258
 Barabasi, A.-L. 631
 Baral, D. 536
 Barenblatt, G. I. 247
 Baribeau, J. M. 62, 459
 Barnett, D. M. 402
 Barnett, S. A. 163
- Batt, C. 58, 59
 Bauer, C. L. 267
 Bauer, E. 20
 Bauschinger, J. 503
 Bean, J. C. 414, 415, 459, 472, 473
 Beardsley, M. B. 115
 Belcher, A. 257, 258
 Beltz, G. E. 391, 455, 461
 Bergveld, P. 378
 Berry, B. S. 42
 Beuth, J. L. 194, 195, 288
 Bhattacharya, A. K. 547
 Bimberg, D. 637
 Biot, M. A. 350
 Black, J. R. 709
 Blakely, J. M. 85, 604, 611, 672
 Blakeslee, A. E. 399, 407, 411
 Blech, I. A. 106, 109, 111, 131, 132, 139, 140, 141,
 149, 203, 205, 522, 531, 697, 701, 702, 703, 704,
 705, 706
 Bodensohn, J. 577
 Bogy, D. B. 223
 Bonar, J. M. 472
 Borovkov, A. I. 637
 Bowden, N. 351, 352
 Bower, A. F. 459, 662
 Bragg, W. 455
 Brasen, D. 485, 487
 Bratkovski, A. M. 636, 671, 672, 673
 Bravman, J. C. 175, 177, 517, 524, 525, 527, 529,
 530, 531, 537
 Brennan, S. 174
 Brittain, S. 351, 352
 Brückner, W. 528, 536
 Budiansky, B. 115
 Buescher, C. 472
 Bulsara, M. T. 487, 602
 Buratto, S. K. 577, 627
- Cahill, D. G. 628
 Cahn, J. W. 26, 648, 684, 685, 688, 690
 Cammarata, R. C. 66, 67, 413
 Campagnolo, C. 58, 59

- Campbell, D. S. 42
 Cannon, R. M. 274
 Cao, H. C. 254
 Carel, R. 78
 Cargill III, G. S. 213, 214
 Carr, E. C. 636
 Chai, H. 328
 Chai, Y. S. 254, 255
 Chang, J. Y. 577, 627
 Charalambides, P. G. 254, 275
 Chason, E. 62, 63, 64, 66, 67, 71, 73, 95, 108, 595,
 597, 598, 632, 633, 635, 671
 Chaudhari, P. 74, 531
 Chen, E. P. 279
 Chen, H. 679
 Chiang, C. 214
 Chiu, C.-H. 585, 586, 665
 Cho, B. 628
 Choi, B. W. 456, 680
 Choi, H. C. 268
 Choi, Y. 507, 534, 679, 680
 Chollacoop, N. 546, 547
 Choquette, K. D. 39, 40
 Chou, Y. T. 427, 428, 429
 Christensen, R. J. 346
 Christian, J. W. 682
 Chuang, T.-J. 557
 Chung, J.-W. 348, 349
 Ciobanu, C. 610, 614, 615, 616, 640, 672
 Citrin, P. H. 577, 627
 Clarke, D. R. 214, 216, 346
 Clemens, B. M. 70, 71, 175, 597
 Cohen, R. E. 680
 Cohen, U. 106
 Colton, R. J. 456
 Copel, M. 416, 472, 476, 637
 Corcoran, S. G. 456
 Cornelison, D. M. 415, 480
 Cornella, G. 175, 177
 Cornie, J. A. 341, 342
 Cottrell, A. H. 533
 Craighead, H. G. 58, 59
 Cullis, A. G. 579
 Cullity, B. D. 172
 Currey, J. D. 256, 257
 Currie, M. T. 487, 602
 Czaplowski, D. 58, 59

 Dao, M. 546, 547
 Daruka, I. 631
 Das Sarma, S. 613, 616
 Dauskardt, R. H. 276, 277
 Davies, P. W. 517
 Davis, J. R. 548
 Davis, S. H. 581, 608
 Dawson, L. R. 411
 Deal, M. D. 522
 Dehm, G. 251, 252, 410, 411, 518, 525, 526
 Delannay, F. 296
 Demchishin, A. M. 45
 Desjardins, P. 628

 Devaney, J. R. 703
 Devries, K. L. 253
 DeWolf, I. 214, 216
 D'Heurle, F. M. 697
 Ding, K. 615
 Dodson, B. W. 409, 415, 480
 Doerner, M. F. 61, 76, 174, 496, 529, 546
 Doljack, F. A. 69
 Duckworth, W. 278
 Dundurs, J. 195, 243, 429

 Eaglesham, D. J. 459, 472
 Elsasser, W. M. 447
 Erdogan, F. 115, 225, 227
 Ernst, F. 34
 Eshelby, J. D. 388, 433, 449, 563, 566
 Eskin, S. G. 102, 103
 Evans, A. G. 13, 115, 248, 251, 252, 254, 258, 271,
 275, 280, 281, 282, 305, 323, 346, 347, 348, 349,
 351, 352, 503, 506, 508, 572

 Farris, R. J. 267
 Fatemi, M. 354
 Feldman, L. C. 413, 634
 Finot, M. 11, 95, 109, 131, 132, 133, 139, 140, 141,
 149
 Fiory, A. T. 413, 414
 Fitzgerald, E. A. 452, 454, 455, 485, 486, 487, 577,
 599, 602, 627
 Flannery, B. P. 669
 Fleck, N. A. 533
 Flinn, P. A. 63, 106, 214, 517
 Floro, J. A. 62, 63, 64, 66, 67, 71, 73, 95, 107, 108,
 597, 632, 633, 635, 671
 Frank, F. C. 406
 Fraser, D. B. 517
 Frederick, N. A. 257, 258
 Freund, L. B. 63, 71, 95, 108, 118, 122, 126, 128, 131,
 136, 149, 153, 235, 236, 243, 256, 286, 391, 395,
 409, 410, 415, 431, 440, 441, 444, 455, 459, 461,
 471, 472, 477, 483, 503, 535, 566, 581, 589, 590,
 595, 598, 599, 608, 609, 610, 614, 615, 616, 632,
 633, 635, 640, 653, 654, 657, 666, 669, 671, 672
 Fried, E. 610
 Friesen, C. 68
 Fritz, I. J. 411
 Fritze, J. R. 102, 103
 Frost, H. J. 76, 508, 510, 511, 513
 Fujikawa, Y. 615
 Fujimoto, H. 109, 131, 132, 139, 140, 149
 Fujita, K. 402
 Fukuda, Y. 35, 38
 Fung, Y. C. 128, 315, 658

 Gao, H. 524, 525, 526, 585, 586, 589, 592, 665, 673,
 678
 Gardner, D. S. 63, 106, 496, 529
 Gaudette, F. G. 12, 13, 251, 252
 Gell, M. 13, 14, 313
 Gent, A. N. 375, 376
 Gerberich, W. W. 456

- Giannakopoulos, A. E. 95, 111, 116, 141, 456, 457, 489, 546
 Giannakopoulos, K. P. 599
 Gibbings, C. J. 403, 415, 419, 459
 Gibbons, J. F. 414
 Gibbs, J. W. 21, 553, 607, 642
 Gibson, J. M. 692
 Gillard, V. T. 477, 483
 Gille, G. 348, 349
 Gilmer, G. H. 577, 627
 Gioia, G. 362
 Giovane, L. M. 602
 Glas, F. 688
 Glass, G. 628
 Golovchenko, J. A. 62, 105, 107
 Goodhew, P. J. 599
 Goodier, J. N. 563, 568, 575, 588, 589
 Gore, G. 86
 Gosling, T. J. 432, 440, 441, 480
 Gouldstone, A. 455, 456, 457, 516, 518, 519
 Gourley, P. L. 411
 Grabow, M. H. 634
 Green, M. L. 485, 487
 Greene, J. E. 628
 Greer, A. L. 536
 Griffith, A. A. 233, 572
 Grinfeld, M. 577
 Grone, A. R. 705
 Groves, G. W. 155
 Gudmundson, P. 194, 195, 208, 209, 212
 Guillaume, C. E. 102, 104
 Gumbsch, P. 525
 Gupta, A. 296, 341
 Gupta, G. D. 225, 227
 Gupta, V. 341, 342
 Gurtin, M. E. 350, 610

 Hager, J. 668
 Han, J. 39
 Hansma, P. K. 257, 258
 Harker, A. H. 480
 Hashimoto, T. 615
 Hau-Riege, S. P. 710
 He, M.-Y. 262, 263, 271, 272, 279, 280, 300, 301, 305, 346, 347, 503, 506, 508
 He, Y. 679
 Head, A. K. 424
 Hearne, S. J. 64, 66, 67, 71, 73, 597
 Heiland, B. 522
 Hellemans, A. 57
 Hemker, K. J. 516, 518, 519
 Henstrom, W. L. 692
 Herman, H. 11
 Herring, C. 21, 22, 26, 553, 557
 Herrman, H. 102
 Heuer, A. H. 258
 Hill, R. 457
 Hillert, M. 690
 Hilliard, J. E. 536, 684, 685
 Hinkley, J. A. 377
 Hirayama, M. 214

 Hirth, J. P. 401, 405, 427, 453
 Ho, P. S. 517
 Hobart, K. D. 353, 354
 Hockly, M. 459
 Hoffman, D. W. 81, 82
 Hoffman, R. W. 69
 Hommel, M. 528, 536, 537
 Hong, S. 537
 Hosford, W. F. 155
 Houghton, D. C. 62, 403, 414, 459
 Houston, J. E. 456
 Howard, D. J. 561
 Howe, R. T. 377, 378
 Hoyt, J. L. 414
 Hu, C. K. 213, 214
 Huang, H. 528, 536, 537
 Huang, R. 354
 Huang, Y. 278
 Hull, R. 40, 405, 409, 414, 415, 416, 472, 473, 476
 Humphreys, C. J. 459
 Hunston, D. L. 253
 Hunt, G. W. 328, 329
 Hunter, J. A. 64, 66, 67, 71, 73, 597
 Huntington, H. B. 705
 Hurtado, J. A. 535, 651
 Hutchinson, J. W. 13, 108, 115, 194, 221, 248, 256, 262, 263, 269, 270, 271, 272, 274, 280, 282, 300, 301, 305, 312, 314, 323, 328, 330, 335, 337, 341, 343, 344, 346, 347, 351, 352, 377, 533, 632, 633, 635, 671
 Hwang, R. Q. 63, 108, 632, 633, 635, 671
 Hyer, M. W. 143

 Ibuki, S. 214
 Ignat, M. 214, 216
 Ilic, B. 58, 59
 Inoki, T. S. 354
 Inoue, Y. 214
 Irwin, G. R. 239, 242, 246, 285, 294, 566
 Israelachvili, J. N. 598

 Jain, S. C. 480
 Jansson, C. 279
 Jawarani, D. 517
 Jensen, H. M. 339, 362, 371, 376, 377, 384
 Jeong, H. C. 611
 Jesson, D. E. 62, 459
 Jitcharoen, J. 116
 Johnson, H. T. 431, 461
 Johnson, K. L. 223, 226, 350, 455, 548, 592, 593, 597, 598
 Jonsdottir, F. 581, 589, 599
 Joo, Y.-C. 707, 708
 Jordan, E. H. 13, 14, 313
 Josell, D. 536

 Kahn, H. 134
 Kamat, S. 258
 Kamath, S. M. 284
 Kamins, T. I. 636, 637, 671, 672, 673, 692
 Kato, T. 214

- Kawasaki, H. 517
 Kaxiras, E. 637
 Kaysser, W. A. 114
 Keller, R.-M. 524, 528, 529, 534
 Keller-Flaig, R.-M. 516, 518, 519
 Kelly, A. 155
 Kendall, K. 593, 598
 Keramidas, V. 37
 Kesler, O. 11
 Ketterson, J. B. 536
 Khor, K. E. 613, 616
 Kiely, J. D. 456
 Kienzle, O. 503, 506, 508
 Kim, D.-K. 522
 Kim, J. O. 163
 Kim, J.-J. 679, 680
 Kim, K. S. 228, 268, 269, 311, 386, 597, 651
 Kindt, J. 257, 258
 King, R. B. 546
 Kinloch, A. J. 247
 Kirchner, P. D. 455, 602
 Kittel, C. 162
 Klokhholm, E. 42
 Kobayashi, K. 214
 Kobrinsky, M. J. 524, 525, 529
 Koch, R. 42, 63, 66
 Koh, H.-J. 456, 457
 Kohama, Y. 38
 Kohn, W. 431
 Koiter, W. J. 227
 Kolawa, E. 111, 112
 Kopev, P. S. 637
 Kortan, A. R. 485, 487, 577, 627
 Kotula, P. 64, 66, 67, 71, 73, 597
 Kraft, O. 178, 503, 528, 536, 537, 538, 540, 708
 Kramer, R. 42
 Krishna, N. 276, 277
 Kuan, T.-S. 517, 528, 531
 Kuan C.K. 354
 Kub, F. J. 354
 Kuhlmann-Wilsdorf, D. 65, 66
 Kukta, R. V. 657
 Kumar, V. 522
 Kummer, M. 672, 692
 Kurdjmov, 39
 Kvam, E. P. 405, 459

 Laderman, S. S. 414
 Lagally, M. G. 615, 616, 627, 671
 Landis, H. S. 341, 342
 Lane, M. 276, 277
 Langdo, T. A. 487, 602
 Laughlin, D. E. 46, 47
 Laugier, M. 66
 Laursen, T. A. 546, 547
 Lavoie, C. 599
 Lawn, B. 233, 594
 Ledentsov, N. N. 637
 Lee, H. 131, 149
 Lee, J.-H. 438, 441
 Lee, K.-R. 348, 349

 Lee, S. R. 63, 108, 632, 633
 Lee, S.-H. 175, 177
 Lee, Y.-C. 163
 LeGoues, F. K. 630
 Legros, M. 516, 518, 519
 Leiderer, P. 577
 Leitz, C. W. 487, 602
 Leonhard, H. 63
 Lewandowski, L. H. 375, 376
 Li, J. 457, 458
 Liang, J. 354
 Liechti, K. M. 254, 255
 Light, T. B. 407
 Lilleodden, E. T. 456
 Liniger, E. G. 335, 337, 341, 342, 343, 344
 Liu, C. P. 278, 692
 Liu, C. T. 680
 Liu, J. 256, 257
 Lloyd, J. R. 702, 709
 Lothe, J. 401, 402, 405, 427, 453
 Lucadamo, G. A. 632, 635, 671
 Lucas, G. E. 281
 Lund, J. 254, 275
 Luttinger, J. M. 431

 Ma, Q. 214, 216, 276, 277
 Machlin, E. S. 70
 Macionczyk, M. 528, 536
 Mader, S. 407
 Maes, H. E. 214, 216
 Mahajan, S. 387
 Maher, D. M. 459
 Maniguet, L. 214, 216
 Marchenko, V. I. 611
 Marcus, M. A. 577, 627
 Mäser, J. 42
 Martin, J. B. 504
 Martinez, R. E. 62, 105, 107
 Mast, P. W. 253
 Masters, C. B. 136
 Masumoto, T. 341, 344, 345
 Mathes, D. 40
 Matthews, J. W. 399, 407, 411, 413
 Maugis, D. 597
 Mays, C. W. 65, 66
 McCaldin, J. O. 431
 McCune, R. 11
 McGill, T. C. 431
 McHenry, M. E. 46, 47
 McKnelly, L. T. 707
 McMeeking, R. M. 254, 275, 597
 Medeiros-Ribeiro, G. 636, 671, 672, 673
 Mehregany, M. 377, 378
 Meier, G. H. 13, 346
 Meieran, E. S. 106
 Meiron, D. I. 665
 Michalske, T. A. 279
 Michel, J. 485, 487
 Minor, A. M. 456
 Mirkarimi, P. B. 163
 Mizawa, N. 50, 51

- Mizoguchi, T. 341, 344, 345
 Mo, Y. W. 616
 Moon, M.-W. 348, 349
 Moore, N. R. 111, 112
 Morikawa, Y. 615
 Morris, J. W. 456, 707
 Morrone, A. 275
 Morse, D. E. 257, 258
 Mortensen, A. 114
 Movchan, B. A. 45
 Mühlberger, M. 614
 Muller, G. M. 533
 Mullins, W. W. 76, 557, 645, 648
 Müllner, P. 534
 Mulville, D. R. 253
 Mumm, D. R. 13, 346
 Murakami, M. 173, 517, 528, 531
 Muskhelishvili, N. I. 226, 228

 Nagamune, Y. 438, 441
 Nagao, T. 615
 Nahory, R. 37
 Nakahara, S. 413, 414
 Nakamura, T. 284
 Needleman, A. 249, 532, 662
 Neuzil, P. 58, 59
 Nicola, L. 532
 Nicolai, K. 577
 Nieh, T.-G. 456, 680
 Nir, D. 349
 Nishimura, T. 214
 Nishioka, M. 438, 441
 Nishiyama, G. 39, 42
 Nix, W. D. 61, 63, 70, 71, 76, 106, 175, 177, 178, 374, 377, 415, 418, 419, 424, 444, 448, 477, 483, 496, 517, 522, 524, 525, 526, 529, 531, 537, 546, 547, 592, 597, 673, 678
 Noble, D. B. 414, 415, 416, 418, 419
 Norris, A. N. 608
 Norstrom, H. 214
 Noyan, I. C. 213, 214, 536
 Nozieres, P. 557, 586, 647, 648
 Nurmikko, A. 39
 Nye, J. F. 455

 O'Dowd, N. P. 275, 279
 Ogawa, K. 341, 344, 345
 Ogawa, T. 309
 Oh, K. H. 348, 349
 Oh, T. S. 274
 Ohba, T. 50, 51
 Ohlberg, D. A. A. 636, 637, 671, 672, 673
 Ohmachi, Y. 38
 Ohring, M. 9, 710
 Okhoshi, T. 341, 344, 345
 Oliver, W. C. 546, 547
 Olsson, E. 296, 341
 Olsson, M. 95, 116, 489
 Olthuis, W. 378
 O'Reilly, E. P. 431
 Orowan, E. 246, 481

 Ortiz, M. 362
 Osterberg, P. M. 377, 381
 Ostwald, W. 42, 634

 Padture, N. P. 13, 14, 116, 313
 Paine, D. C. 561
 Pan, J. T. 106
 Paris, P. 285, 294
 Park, T. S. 146, 209, 211
 Parshin, A. Ya. 611
 Pennycook, S. J. 62, 459
 Perovic, D. D. 459
 Peterson, K. E. 378
 Peticolas, L. J. 415
 Petroff, P. M. 522
 Pettit, F. S. 13, 346
 Pettit, G. D. 455, 602
 Pharr, G. M. 546, 547
 Phillips, M. A. 71
 Phillips, R. 503
 Picraux, S. T. 415, 480
 Pidduck, A. J. 579
 Pimpinelli, A. 15
 Pinnington, T. 599
 Plummer, J. D. 522
 Poon, S. J. 679
 Pozza, G. 214, 216
 Press, W. H. 669
 Prevost, Jean 431
 Proano, R. E. 455, 602

 Rabenberg, L. 517
 Ramaswamy, V. 71
 Ramirez, J. C. 459
 Rastelli, A. 672, 692
 Rau, B. 348, 349
 Rayleigh, Lord 21
 Read, D. T. 536
 Retajczyk, T. F. 106
 Reuter, M. C. 416, 472, 473, 476, 627, 633, 634, 637, 671
 Rice, J. R. 224, 242, 243, 327, 457, 461, 509, 557, 566, 662
 Rich, T. A. 94
 Ritchie, R. O. 274
 Robbins, D. J. 579
 Roberts, A. D. 593, 598
 Robinson, I. K. 413
 Rödel, J. 274
 Roland, C. 577, 627
 Romano-Rodriguez, A. 214
 Rosakis, A. J. 111, 112, 131, 149
 Rosenfeld, A. 278
 Rosner, S. J. 636
 Ross, F. M. 473, 603, 627, 633, 634, 671
 Rowcliffe, D. 134
 Rühle, M. 34, 38, 251, 252, 503, 506, 508
 Ruud, J. A. 536

 Sachs 39
 Sakurai, T. 615

- Salamon, N. J. 136
 Samavedam, S. B. 487, 599, 602
 Sampath, S. 11, 12, 13
 Sanchez, J. E. 278, 707, 708
 Sarikaya, M. 256, 257
 Savage, D. E. 616
 Schadler, L. S. 536
 Schaffer, T. E. 257, 258
 Schäffler, F. 614
 Scheeper, P. R. 378
 Schelling, C. 614
 Schell-Sorokin, A. J. 62, 107
 Schneeweiss, H. J. 72
 Schuppler, S. 577, 627
 Schwaiger, R. 528, 538, 540
 Schwartzman, A. 38
 Schwarz, K. W. 472
 Schweinfest, R. 38
 Schwoebel, R. L. 18, 647
 Schwuttke, G. H. 106
 Scott, M. P. 414
 Seel, S. C. 64, 66, 67, 71, 73, 597
 Seki, M. 38
 Senturia, S. D. 377, 378, 381
 Sharpe, W. N. 536
 Shchukin, V. A. 637
 Sheldon, B. W. 71
 Shen, Y.-L. 203, 205, 496, 503, 506, 508, 514, 517, 523, 524, 525, 548
 Shenoy, V. B. 289, 609, 610, 614, 615, 616, 640, 666, 669, 672
 Shetty, D. K. 278
 Shield, T. W. 228, 269, 311
 Shiffet, G. J. 679
 Shih, C. F. 275, 279, 662
 Shintani, K. 402
 Short, K. T. 415
 Shull, A. L. 71, 73, 106, 116
 Shuttleworth, R. 26
 Sieradzki, K. 413
 Sigle, W. 518
 Simo, J. C. 546, 547
 Sinclair, M. 632, 635, 671
 Sinclair, R. 38
 Singh, J. 104
 Singh, R. B. 111, 112
 Singh, R. K. 51
 Sinha, A. K. 106
 Small, M. K. 374
 Smelser, R. 278
 Smith, B. L. 257, 258
 Smith, P. W. 579
 Smith, W. L. 279
 Spaepen, F. 67, 71, 73, 106, 528, 536, 537, 680
 Spearing, S. M. 56
 Spencer, B. J. 581, 665
 Spohn, H. 668
 Springholz, G. 599, 614
 Sridhar, N. 353
 Srikar, V. T. 709, 710
 Srolovitz, D. J. 67, 353, 577, 650, 665
 Stach, E. A. 412, 416, 456, 472, 473, 476
 Starck, J. P. 517
 Stillinger, F. H. 615
 Stippes, M. 429
 Stoffel, N. G. 561
 Stölken, J. S. 253
 Stoney, G. G. 86, 91
 Storåkers, B. 377
 Stout, M. G. 278, 279
 Stringfellow, R. G. 243, 256
 Stucky, G. D. 257, 258
 Sturm, J. C. 354, 431
 Su, X. 258
 Sugimura, Y. 309
 Sun, B. 572
 Suo, Z. 214, 216, 221, 254, 258, 269, 270, 278, 281, 282, 328, 330, 353, 354, 377, 567, 572, 697, 710
 Suresh, S. 11, 12, 13, 95, 109, 111, 114, 116, 131, 132, 133, 139, 140, 141, 149, 194, 195, 203, 205, 208, 209, 212, 239, 251, 252, 275, 309, 310, 455, 456, 457, 458, 489, 496, 503, 506, 508, 514, 516, 517, 518, 519, 523, 524, 525, 534, 539, 546, 547, 548, 662, 679, 680
 Sutter, P. 627, 671
 Swartzentruber, B. S. 616
 Tabock, J. 81, 82
 Tabor, D. 548
 Tada, H. 285, 294
 Tai, K. L. 522
 Takeuchi, T. 341, 344, 345
 Tan, H. 651
 Taraschi, G. 487, 602
 Taylor, J. E. 648
 Terakura, K. 615
 Tersoff, J. 472, 615, 630, 631
 Teukolsky, S. A. 669
 Thompson, C. V. 43, 44, 45, 64, 66, 67, 68, 70, 71, 73, 76, 78, 524, 525, 526, 529, 534, 597, 673, 678, 702, 707, 708, 709, 710
 Thompson, J. B. 257, 258
 Thompson, J. M. T. 328, 329
 Thompson, P. E. 354
 Thomson, R. 461
 Thornton, J. A. 45, 81, 82
 Thouless, M. D. 254, 296, 323, 335, 337, 342, 343, 344, 384, 513, 524, 673, 676, 678
 Turner, G. 63, 72
 Tiedje, T. 599
 Tien, N. C. 379
 Tiller, W. A. 557, 577
 Timoshenko, S. P. 94, 102, 563, 568, 575, 588, 589
 Toplygo, V. K. 346
 Torii, R. H. 577
 Trantina, G. C. 253
 Trimble, T. M. 67
 Tromp, R. M. 62, 107, 415, 472, 473, 476, 627, 633, 634, 637, 671
 Tsao, J. Y. 15, 409, 415, 480, 682
 Tsui, T. Y. 546
 Tsuji, Y. 111, 112

- Tsukamoto, S. 438, 441
 Tuppen, C. G. 403, 415, 419, 459
 Turlo, J. F. 415, 416, 418, 419
 Turner, M. R. 279, 280
 Tvergaard, V. 256
 Twesten, R. D. 63, 108, 632, 633, 635, 671
 Twigg, M. E. 354

 Unterwald, F. C. 415

 Vaillionis, A. 628
 van der Berg, N. G. 406
 van der Donk, A. G. H. 378
 Van der Giessen, E. 532
 Van der Merwe, J. H. 406
 Van Mellaert, L. J. 106
 Van Vliet, K. J. 455, 456, 457, 458, 546, 547
 Vanhellemont, J. 214
 Venables, J. A. 15, 30
 Venkatesh, T. A. 546, 547
 Venkatraman, R. 517, 527, 529, 530, 531
 Vermaak, J. S. 65, 66
 Vetterling, W. T. 669
 Viani, M. 257, 258
 Villain, J. 15
 Vinci, R. P. 524, 525
 Vlassak, J. 377, 546
 Volkert, C. A. 106
 von Blanckenhage, B. 525
 von Kanel, H. 672, 692
 von Mises, R. 499
 Voorhees, P. W. 581

 Wagner, T. 34, 410, 411
 Walton, D. T. 76
 Wang, J. G. 680
 Wang, J.-S. 254, 278
 Wang, P. C. 213, 214
 Wang, R. Z. 258, 348, 349
 Wang, W. 567
 Warren, P. 296
 Wasserman, G. 39
 Watson, G. P. 455, 602
 Weatherly, G. C. 297, 428, 429, 459
 Weber, T. A. 615
 Weeks, R. 429

 Wei, Y. 274
 Weihs, T. P. 537
 Weiss, D. 524
 Whitcomb, J. D. 344
 Whitesides, G. M. 282, 351, 352
 Wikström, A. 194, 195, 208, 209, 212
 Wilcock, J. D. 42
 Williams, E. D. 611
 Williams, M. L. 253, 289, 303
 Williams, R. S. 636, 637, 638, 671, 672, 673, 692
 Willis, J. R. 432
 Wilson, C. A. 102
 Woodall, J. 455, 602
 Wu, C. H. 608, 610
 Wu, X. 297, 428, 429
 Wulff, G. 21

 Xia, L. 662
 Xia, Z. C. 194
 Xie, Y. H. 485, 487, 577, 602, 627

 Yagi, H. 50, 51
 Yang, M. Y. 431, 665
 Yang, V. 487, 602
 Yang, W. 459
 Yao, N. 258
 Yeo, I.-S. 517
 Yin, H. 354
 Yin, W. L. 328
 Yip, S. 457, 458
 Young, T. 21, 25
 Yu, E. T. 431
 Yu, H. H. 262, 263, 271, 272, 314

 Zak, A. R. 289, 303
 Zangwill, A. 646
 Zaslavsky, A. 431
 Zeng, K. Y. 456, 457
 Zhang, H. 459
 Zhang, L. 524, 525, 526, 673, 678
 Zhang, Y. W. 662
 Zhou, Q. Y. 680
 Zhu, T. 457, 458
 Zhuk, A. V. 282
 Zielinski, E. M. 524, 525
 Zinke-Allmang, M. 42, 634

Subject index

- adatoms, *see* clusters of adatoms 15–20
 adhesive layer 238
 amorphous films 5, 15, 44
 amorphous substrate 41
 anisotropic film
 mismatch stress 166
 substrate curvature 180
 anisotropy, elastic 155
 anisotropy ratio 161
 cubic symmetry 157
 cubic crystals (table) 159
 effective modulus 158
 hexagonal symmetry 162
 hexagonal symmetry (table) 163
 associated plastic flow rule 498
 atomic peening 82
 atomically thin films 5–6

 bacterium detector 58, 59
 bandgap energy 36–7
 bias sputtering 9
 biaxial elastic modulus 89
 bifurcation of equilibrium shape, *see also*
 geometrically nonlinear deformation 132–42
 bimaterial strip 102
 Black's equation (electromigration) 709
 blocking of a threading dislocation 472
 Boltzmann constant 17
 Brazilian disk specimen 278
 buckling of a film 313, 323
 experimental observations 341
 buckling wavelength 354
 bulge test 377
 Burgers vector
 edge component 392
 screw component 392

 capping layer 418, 487
 cohesive zone models 247
 chemical potential 17, 568
 chemical potential of a surface
 bimaterial interface 559
 and crack growth 564

 free surface 553
 migrating interface 560
 and surface anisotropy 608
 and surface strain 608
 chemical vapor deposition (CVD) 6, 9–10, 13–15, 55,
 114
 laser enhanced (LECVD) 10
 low pressure (LPCVD) 10
 metal organic (MOCVD) 10
 plasma enhance (PECVD) 10
 classification of thin films 2–6
 clusters of adatoms
 adatoms 15–20
 critical size 42
 nucleation 18–19
 growth 27–30
 CMOS 48, 55
 coatings
 diamond-like carbon (DLC) 348–50
 for gas turbine engine 1, 13–15
 graded 1, 11
 thermal barrier 13–15, 343
 coercivity 46
 coherent interface, *see* interface
 columnar grains 15, 45
 compositionally graded films, *see* graded films
 compound semiconductors 37, 92
 condensation 647
 contact of surfaces
 cohering surfaces 592
 Hertz theory 592
 crack deflection
 at an interface 297
 into an interface 302
 out of an interface 299
 cracks in film
 array 292
 biaxial curvature 197
 deflection 297
 effect on substrate curvature 190
 phase angle 243
 stability 236
 through-thickness 283

- critical thickness for cracking 286
critical thickness for dislocation formation 397, 408
 dependence on strain 400
 dependence on orientation 404
 effect of capping layer 418
 effect of modulus difference 426
 effect of substrate compliance 441
 effect of viscous underlayer 445
 experimental observation 403
 graded film 423
 layered film 416
 limitations 411
 Matthews–Blakeslee criterion 399
 nonplanar systems 430
 superlattice 422
critical wavelength for surface instability 577
 fastest growing wavelength 650
 influence of substrate stiffness 578
crystallographic texture 41, 46, 76–9
curvature measurement, striped film
 X-ray diffraction method 213
 micro-Raman method 214
curvature measurement, uniform film
 capacitive method 105
 coherent gradient sensor method 111, 142
 grid reflection method 109, 140
 multibeam optical stress sensor (MOSS) 107
 scanning laser method 106
 X-ray diffraction method 105
- damascene process 50–2
delamination of interface 243
 curvature of front 264
 due to buckling 319, 333
 due to bulging 363, 374
 due to peeling 383
 due to residual stress 258
 due to thermal strain 263
 phase angle 268
 spontaneous 258
- diffusion
 see electromigration
 see interface diffusion
 see surface diffusion
- dislocation density
 and patterning 485
 threading dislocations 481, 486
- dislocation interactions
 dislocation blocking 472
 equilibrium spacing 465–70
 intersecting arrays 478
 intersecting misfit dislocations 470
 parallel misfit dislocations 465
 and strain relaxation 480
- dislocation mechanics 388
 configurational force 388
 elastic field 391
 energy of a dislocation 393
 force on dislocation 388
 image force 389
 self force 389
- dislocation nucleation 451
double cantilever beam 234, 273
double cleavage drilled compression test 279
- deposition, of films
 chemical vapor deposition 6, 9–10, 13–15, 55
 electron beam deposition 7, 14–15
 evaporative deposition 9, 43–5, 71–2
 growth flux 30
 molecular beam epitaxy 7–8
 physical vapor deposition 6–9, 13–15
 shadowing effect 44
 sputter deposition 8, 47, 79–81
 substrate temperature 7, 30
 thermal spray 10–15
 vapor pressure 7
- diffusion barrier 19
direct current (DC) sputtering 8–9
dislocation control in semiconductor films 484
dislocation, misfit 35, 115
Dundurs parameters 195, 244
 table of values 244
- edge effects 88
 Kirchhoff plate 227
 load transfer 223
 membrane film 223
 and phase angle 271
 and size scale 231
 stress at film edge 221–32
- elastic compliance 157
elastic modulus
 biaxial modulus 89
 shear modulus 87
 table of values 96
- elastic shakedown 494
electromigration 697
 atom transport 698
 drift test 704
 hillock formation 703
 microstructural effects 707
 stress evolution 701
 threshold line length 703
 void formation 704, 707, 708
- electron beam deposition 7, 14–15
energy density of a surface, *see* surface energy
energy release rate 233, 235, 242, 333
epitaxial films 31–40, 45–7
 cracking 297–302
 epitaxy 31
 heteroepitaxy 31
 homoepitaxy 31, 83
 mismatch strain 164
 stress in 62–3
 epitaxial mismatch strain 164
equilibrium vapor density 17
equilibrium vapor pressure 16
equivalent plastic strain rate 499
equivalent stress (Mises stress) 499
evaporation 647
evaporative deposition 9, 43–5, 71–2

- films
 - amorphous 5, 15, 44
 - atomically thin 5–6
 - classification of 2–6
 - compound semiconductors 37
 - dislocation control 484
 - epitaxial 31–40, 45–7
 - graded 114–27
 - layered 114–27
 - magnetic 45–7, 84
 - mechanically thin 4–5
 - microstructurally thin 5
 - piezoelectric 1, 61, 187
 - piezoresistive 1, 61
 - polycrystalline 40–5
 - semiconductor 36, 37, 41
- film buckling 313
 - circular buckle 327
 - experimental observations 341
 - and imperfections 345
 - secondary buckling 338
 - telephone cord buckle 348
 - uniform strip 313
 - viscous substrate 353
 - without delamination 350
- film bulging 355
 - capacitive transducer 378
 - circular bulge 366
 - experimental results 377
 - and delamination 363, 374
 - large deflection response 357, 371
 - membrane response 360, 367
 - residual stress effect 372
 - small deflection response 355, 367
 - uniform strip 355
- film cracking
 - array of cracks 292
 - due to residual stress 282
 - tunnel cracks 290
- film delamination 258
 - due to buckling 319
 - due to peeling 382
 - residual stress 258
- film deposition, *see* deposition
- film peeling 382
- flexure beam test 274
- force on dislocation
 - configurational force 388
 - dislocation in a layer 449
- fracture mechanics 232
 - cohesive zone models 247
 - energy release rate 233
 - fracture energy 233
 - fracture toughness 237, 242
 - Griffith criterion 233
 - J-integral 224
 - stress intensity factor 239
 - work of fracture 233, 246
- Frank–van der Merwe (FM) growth 16, 19, 29, 31
- free energy 18–19, 642
- fully confined films 3
 - gas turbine engines 1, 13–15
 - geometrically nonlinear deformation 127
 - axially symmetric 130
 - bifurcation 132, 134, 145
 - curvature map 150
 - gravity effects 141–2
 - Mohr’s circle 143
 - Gibbs–Thomson relation 563
 - graded films 114–27
 - critical thickness 423
 - grain boundary diffusion 526, 673
 - stress relaxation 674
 - Griffith criterion 233, 567, 572
 - growth flux 30, 71
 - growth modes
 - Frank–van der Merwe (FM) 16, 19, 29, 31
 - Stranski–Krastanov (SK) 16, 20, 30
 - Volmer–Weber (VW) 15, 20, 28, 41, 63
- interconnect reliability 709
- interface
 - coherent 33
 - diffusion along interface 673
 - diffusion along shear bands 678
 - energy, *see* surface energy
 - mass transport 558
 - migration 560
 - semi-coherent 35
 - interface delamination 243
 - fracture toughness (table) 254
 - interfacial shear stress 226
 - peel test 382, 386
 - processing and chemistry effects 250–3
 - toughness measurement 272
 - interface diffusion 673
 - along shear bands 678
 - grain boundary diffusion 674
- Invar 103–4
- island
 - coalescence 65–9
 - experimental observations 632
 - formation 24–5
 - free energy change for island growth 666
 - growth with stepped surfaces 665
 - impingement 597
 - interaction 668
 - strained epitaxial island 615
 - surfactants, effects of 637
- islands, epitaxial
 - elastic interactions 635, 668
 - formation due to strain 615
 - nucleation barrier 628
 - scaling properties 619
 - shape transition 630, 634
 - spontaneous growth 665
 - and substrate properties 623, 624
 - and surface energy anisotropy 626
- Kirchhoff hypothesis 88
- Kurdjumov–Sachs orientation 39

- large deformation, *see* geometrically nonlinear deformation
- layered films 114, 164
- LIGA 55–6
- light-emitting diode (LED) 486
- lithography 48–50
- longitudinal magnetic recording 45–7
- low pressure plasma spray 12
- magnetic data storage 1, 45–7
- magnetic thin films 45–7, 84
- magnetron sputtering 9, 45
- maximum plastic resistance postulate 497
- membrane force
- small deformation 87–91
 - geometrically nonlinear deformation 132
- mechanically thin films 4–5
- microbeam deflection method 537
- micromachining
- bulk 52–3
 - surface 52–3
- micromachined mirror 54
- MEMS (microelectromechanical systems)
- bulk micromachining 52–3
 - capacitive transducer 378
 - LIGA 55–6
 - molding process 55
 - processing 52–5
 - surface micromachining 53–5
- microelectronic structures
- CMOS 48, 55
 - damascene process 50–2
 - lithography 48–50
 - processing 47–52
- microstructurally thin films 5
- Mises stress (equivalent stress) 499
- misfit dislocation 35
- mismatch strain
- effect on critical thickness 400
 - nonuniform 116
- mismatch stress 11, 60–2
- mismatch strain 32, 34
- molding process 55
- molecular beam epitaxy 7–8
- multilayer film 123–7
- nacre, fracture of 256
- nanoindentation 543, 679
- NEMS, nanoelectromechanical systems 55–60
- neutral plane 91
- Nishiyama–Wasserman orientation 39
- nucleation barrier for islands 628
- optoelectronic films 484
- Ostwald ripening 42
- partially confined films 3
- patterned film
- due to cracking 188
 - due to parallel lines 201
- peel test 382, 386
- perpendicular magnetic recording 45–7
- phase angle 243, 321
- photoresist 48
- physical vapor deposition (PVD) 6–9, 13–15
- piezoelectric thin film
- mismatch strain 187
 - substrate curvature 187
- piezoresistive thin film 1, 61
- plasma spray
- air plasma spray 11–15
 - low pressure plasma spray 12
 - vacuum plasma spray 12
- plastic deformation of films, measurement 535
- microbeam deflection method 537
- nanoindentation 543
- substrate curvature 542
- tensile testing 535
- plastic flow rule 497
- plastic rate equations 508
- grain boundary diffusion 512
 - thermally activated glide 510
- plastic response of films
- flow stress (table of values) 528, 529
 - grain boundary diffusion 526
 - ideally plastic response 488
 - measurement 535
 - models 531
 - plane strain extension 539
 - size dependence 527
 - strain hardening response 496
 - and structure evolution 515
 - temperature cycling 494, 501
 - temperature dependence of 527–31
- plastic yield surface 497
- isotropic hardening 499
 - kinematic hardening 502
 - proportional stress history 505
- plastic zone 242
- Poisson ratio (table of values) 96
- polycrystalline films, types 43–4
- pressurized bulge in film 355, 366
- process zone, embedded process zone 242, 248
- processing
- see* MEMS
 - see* microelectronic structures
- quantum well 486
- quantum wire 430
- effect of free surface 437
 - strained quantum wire 432
- quench stress 11
- radio frequency (rf) sputtering 9
- refractory metals 43–4
- scanning tunneling microscope (STM) 57
- Schwoebel barrier 18
- secondary buckling 338
- semiconductor films 36, 37, 41
- shadowing effect 44
- shear modulus 87

- size dependence of plastic response, models 531
- small deformation 88–91
- small scale yielding 242
- solid solutions
 - chemical potential 686
 - composition-deformation coupling 692
 - compositional variations 681
 - elastic stabilization 689
 - evolution of composition 690
 - free energy 682
 - stability 685
- spinel 33–4
- spinel 11–13
- sputter deposition, *see also* deposition 8, 47, 79–81
- stable crack growth 236
- Stranski–Krastanov (SK) growth 16, 20, 30
- strain
 - contracted notation 156
 - epitaxial 32, 34, 87–92
 - extensional 89
 - mismatch 32, 87–93, 96, 101–2
 - relaxation model 480
 - thermal 93, 263
 - transformation 87
- strain hardening response of films, *see also* plastic
 - yield surface 496
- strained layer superlattice 417
- strain relaxation
 - mechanisms 520
 - model 480
- stress
 - classification 60–2
 - contracted notation 156
 - deviatoric 499
 - extrinsic 60
 - growth 60
 - intrinsic 60
 - origin of 60–3
 - quench 11
 - stress-assisted diffusion 697
 - surface 25–7, 65–6
 - thermal mismatch 11, 60–2, 87–102
 - traction 220
 - and translational invariance 221
- stress-assisted diffusion 697
- stress concentration 220
- stress intensity factor 239
- Stoney formula 90
 - derivation 87–92
 - range of validity 98–100
 - restrictions 88
- striped film
 - substrate curvature 201
 - volume averaged stress 206, 209
 - curvature measurement 212
- structure evolution in films 515
- substrate curvature
 - and epitaxial strain 92
 - and thermal strain 93
 - deformation map 149
 - graded films 114, 120
 - multilayer films 114, 123, 125
 - and plastic response of films 542
 - thick films 97
 - thin films 87
- superlattice, *see* strained layer superlattice
- superlayer test 280
- supersaturated vapor 16
- surface chemical potential 557, 608
- surface cohesion, *see* energy of a surface
- surface condensation 647
 - surface normal speed 648
- surface diffusion 643
 - energy dissipation 645
 - mobility coefficient 644, 646, 647
 - surface flux 644
 - surface normal speed 645
- surface energy 16, 552
 - anisotropy 604
 - influence of strain 605
 - and step formation energy 611
 - and step interaction energy 611
 - vicinal surface 610
- surface evolution
 - characteristic time 650
 - due to subsurface dislocations 598
 - due to surface diffusion 649
 - elliptical hole 567
 - mechanisms 643
 - patterning due to misfit dislocations 602
 - variational approach 657
- surface flux 658
- surface rebonding 21
- surface reconstruction 21
- surface stability 552
 - elliptical cavity 570
 - general perturbation 588
 - nominally flat surface 573
 - second order effects 582
 - substrate stiffness effect 578
 - and surface energy anisotropy 616
- surface stress 25–7, 65–6, 552
- surface tension, *see* surface energy
- surface waviness, due to misfit strain 599
- telephone cord instability 343–5, 349
- tensile testing of films 535
- texture, *see* crystallographic texture
- thermally activated dislocation glide 510
- thermal barrier coating (TBC) 13–15, 343
- thermal cycling of films 494, 501
 - strain relaxation mechanisms 520
- thermal expansion coefficient (table) 94, 95
- thermally grown oxide (TGO) 13–15, 346
- thermal mismatch stress 11, 60–2
- thermal spray 10–15
- thermodynamic equilibrium 552, 643
- thermostatic bimetals 102–4
- thin film criterion 99
- threading dislocation 406
 - activation energy for glide 416
 - blocking of 472

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Index

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750

Subject index

- threading dislocation (*cont.*)
 excess stress on 409
 experimental observation 517
 in semiconductor films 487
 nonequilibrium conditions 413
top coat 13–15
tunnel crack 290
two-substrate method 151
- ULSI 52
unconfined films 3
- vacuum plasma spray 12
vapor deposition
 methods, *see* deposition methods
 modes of film growth 15–30
variational approach to surface evolution 657, 669
VCSEL, vertical cavity surface emitting laser 39–40
- vicinal surface 610
viscous substrate 353
VLSI 48
Volmer–Weber growth (VW) 15, 20, 28, 41, 63
- wetting angle 25
work of fracture 246
 embedded process zone 248
 phase angle effects 253
 processing effects 250
wrinkles in film 342, 349
Wulff construction 21–3
- X-ray diffraction 171
 asymmetric diffraction 174
 d-spacing 172
 grazing incidence X-ray scattering 173
 stress-free *d*-spacing 174